- Samenumrt Deutsich	m Actur 1995, no per‰		PTC/SB/08A (16-0) Approved for use through 10/31/2002, OMB 08-110-1 Tradenisk Office: U.S. DEPARTMENT OF COMMERC formation unloss it contains a valid OMB control number	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if known	
			10/065,920	
			November 29, 2002	
			Rolf-P. VOLLERTSEN	
			Not Assigned Yet	
			Not Assigned Yet	
			01P19578US	
	ISCLOS APPLIC	ISCLOSURE APPLICANT	SPAPPENORIA Reduction Act of 1995, no parsons are required to respond to a collection of in Comp Application Number Filling Date APPLICANT First Named Inventor Art Unit Examiner Name	

OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS					
		THE PRIOR ANT LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal,	77		
xaminer Initials*	Cite No.1	OTHER PRIOR ART NON PATENT LITERATURE (IN CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(a), volume-issue number(s), publisher, city and/or country where published. J. H. STATHIS; "Reliability limits for the gate insulator in CMOS Technology"; IBM J. Res.			
			Ì		
		& Dev. Vol. 46 No. 2/3; March/May 2002; Pgs 265-286 & Dev. Vol. 46 No. 2/3; March/May 2002; Pgs 265-286 E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHENKER, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHEN, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. WU, E. J. NOWAK, A. VAYSHEN, W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. HARMON; "CMOS Scaling E. Y. W. L. LAI, D. L. L. W. W. W. L. L. W.			
		Beyond the 100-nm Node with Silicon-Dioxide-Based Gate Dielectrics"; IBM J. Res. &			
		Beyond the 100-nm Node with Silicon-Dioxido-Bases Satisfaction and November 100-nm Node with Silicon-Dioxido-Bases Satisfaction and			
		Dev. Vol. 46 No. 2/3; March/May 2002; Pgs 287-298 Dev. Vol. 46 No. 2/3; March/May 2002; Pgs 287-298 This Cate Oxide Reliability – The Current Status"; Symposium on			
	-				
		THE STATE OF			
	1	LYANDAMME & DADENES, "IMPACT OF MUSEE! UNICE DISERSONT OF THE			
	İ		-		
		BARRY P. LINDER, DAVID J. FRAIN, NAMES II & Dielectrics"; 2001 Symposium on "Transistor-Limited Constant Voltage Stress of Gate Dielectrics"; 2001 Symposium on			
		VLSI Technology Digest of Technical Papers 2001	-		
	<u> </u>	VESI (comology signature)	+		
	 		 		
	 		\vdash		
	+				
	+		<u> </u>		
	+		-		
			+-		
	+-				

	2010
Examiner	Considered
Signature	Considered

^{*}EXAMINER: Initial if relational considered, whether or not citation is in conformance with MPEP 609, Draw line through citation if not in conformance and not conformance with meet communication to applicant.

Applicants unique ditation designation number (optional). *Applicant is to place a chack mark here if English language Translation is estached.

Applicants unique ditation designation number (optional). *Applicant is to place a chack mark here if English language Translation is estached.

Applicants unique ditation designation number (optional). *Applicant is to place a chack mark here if English language Translation is estached.

Applicants unique ditation designation number (optional). *Applicant is to place a chack mark here if English language Translation is estached.

Applicants unique displaced in the amount of interpretation of the place and the

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of Not Assigned Yet Examiner: Rolf-P. Vollertscn Not Assigned Yet Art Unit: 10/065,920 Serial No. 01P19578US Atty Dkt No.: November 29, 2002 Filed: Dec 04, 2002 METHOD OF RELIABILITY For: TESTING

CERTIFICATE OF TRANSMISSION

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office, Washington, DC 20231 on

Dec 04, 2002.

Signed

Andrea Won

COMMISSIONER FOR PATENTS Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 37 C.F.R. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorneys for Applicants hereby bring the following references to the attention of the Examiner. The references are listed on the attached modified PTO Form No. PTO/SB/08A. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

A copy of each patent, publication or other information listed on the modified PTO Form No. PTO/SB/08A is enclosed, except as otherwise indicated.

Dated: Dec 04, 2002

Respectfully submitted,

Dexter Chin

Attorney for Applicant

Reg. No. 38,842

Horizon IP Pte I id 166 Kallang Way 6th Floor Singapore 349249 Tel.: (65) 9836 9908

Tel.: (65) 9836 9908 Fax: (65) 6746 8263